

1    **IN THE CLAIMS**

2  
3    **Please amend Claim 1 as follows.**

4  
5       1.    **(Currently Amended)** A memory unit comprising:  
6           a memory portion having storage units for storing  
7 data bits;  
8           a memory portion for storing error correction  
9 bits;  
10          an error checking and correction unit; and  
11          registers to hold the location of one or more  
12 corrected bits;  
13          wherein the error checking and correction unit  
14 includes circuitry for requesting an interrupt and/or for  
15 setting a flag which is polled, when a memory location of a  
16 failing bit is correctable.

17  
18    **Please cancel Claim 2.**

19  
20       2.    **(Cancelled)**    ~~The memory unit as recited in~~  
21 ~~claim 1 wherein the error checking and correction unit~~  
22 ~~includes circuitry for requesting an interrupt and/or for~~  
23 ~~setting a flag which can be polled, when a failing bit can~~  
24 ~~be corrected.~~

25  
26    **Please amend Claim 3 as follows.**

27  
28       3.    **(Currently Amended)** The memory unit as recited in  
29 claim 1 wherein the error detection and correction unit  
30 includes circuitry for requesting an abort condition when a

1 failing bit memory location is detected which can not be  
2 corrected.

3  
4 **Please amend Claim 4 as follows.**

5  
6 4. (**Currently Amended**) The memory unit as recited in  
7 claim ~~2~~ 3 wherein the memory is composed of storage units  
8 storing data bits that ~~can be~~ are set to one of two states,  
9 wherein any of the data bits ~~may be~~ are changed to a first  
10 state independently of the other bits, the resulting state  
11 being a programmed state, wherein all of the data bits of a  
12 plurality of data bits must be set to the second state  
13 simultaneously, the second state being an erased state, the  
14 memory unit further comprising:

15 circuitry to store the location of a correctable  
16 memory location error; and

17 circuitry to generate an interrupt request;

18 circuitry to set a flag bit only when the correctable  
19 memory location error is a bit that has been changed from  
20 the programmed state to the erased state.

21  
22 **Please withdraw Claim 5.**

23  
24 5. (**Withdrawn**) A memory unit comprising:  
25 storage units storing data bits;  
26 storage units storing error checking and correction  
27 bits; and

28 an error detection and correction unit wherein the  
29 memory unit contains circuitry to optionally exclude the  
30 condition where all of the data bits and error detection

1 and correction bits are in the erased state from generating  
2 bit correction.

3  
4 **Please withdraw Claim 6.**

5  
6 6. **(Withdrawn)** A memory unit comprising:  
7 storage units for storing data bits;  
8 storage units for storing error correction bits;  
9 an error detection and correction unit;  
10 circuitry to optionally exclude the condition  
11 where all of the data bits and error detection and  
12 correction bits are in the programmed state from generating  
13 bit correction.

14  
15 **Please amend Claim 7 as follows.**

16  
17 7. **(Currently Amended)** A data processing system, the  
18 data processing system comprising:  
19 a central processing unit; and  
20 a memory unit, the memory unit including:  
21 a main memory, the main memory storing data  
22 signal groups in a plurality of addresses;  
23 an error checking and correction memory, the  
24 error checking and correction memory storing error  
25 correcting signals for each data signal group in the main  
26 memory at the same address in the error checking and  
27 correction code memory;  
28 an error checking and correction apparatus  
29 for identifying and correcting at least one error in a

1 memory location of a data group accessed by a read  
2 operation; and

3 a failing bit apparatus, the failing bit  
4 apparatus identifying when a correctable error is the  
5 result of a failing bit memory location.

6  
7 **Please amend claim 8 as follows.**

8  
9 8. **(Currently Amended)** The data processing system as  
10 recited in claim 7 wherein the failing bit apparatus  
11 includes:

12 an address storage unit;  
13 a correction pattern storage unit; and  
14 an interrupt flag unit, the interrupt flag unit  
15 issuing an interrupt flag when an error is detected that  
16 ~~can be~~ is the result of failing bit memory location.

17  
18 9. **(Original)** The data processing system as  
19 recited in claim 8 further comprising an all logic "1"s  
20 detection unit for determining whether all of the signals  
21 from a main memory and error checking and correction memory  
22 are all logic "1".

23  
24 10. **(Original)** The data processing system as  
25 recited in claim 7 wherein the main memory and the error  
26 checking and correction memory are implemented in a  
27 technology selected from the group consisting of flash  
28 technology and EEPROM technology.

1 Please withdraw claim 11.

2  
3 11. (Withdrawn) A method of responding to an  
4 error in a signal group retrieved from a non-volatile  
5 memory unit, the method comprising:

6 when the error is correctable, correcting the  
7 error in the signal group using error checking and  
8 correction techniques; and

9 when the error is consistent with a failing bit  
10 position, restoring the charge associated with the bit  
11 position.

12  
13 Please withdraw Claim 12.

14  
15 12. (Withdrawn) The method as recited in claim 11  
16 wherein the restoring step includes the steps of:

17 storing the address of the signal group having  
18 the error;

19 storing the correction pattern identifying  
20 location of the error in the signal group; and

21 providing an interrupt flag to the central  
22 processing unit indicating the need to restore a bit  
23 location in the memory unit.

24  
25 Please withdraw Claim 13.

26  
27 13. (Withdrawn) The method as recited in claim 11  
28 further comprising implementing the main memory and the  
29 error checking and correction memory in a technology

1 selected from the group consisting of flash technology and  
2 EEPROM technology.

3  
4 **Please amend Claim 14 as follows.**

5  
6 14. **(Currently Amended)** A memory unit comprising:  
7 a non-volatile main memory unit;  
8 a non-volatile error memory for storing error  
9 checking and correction signals for a signal group in the  
10 main memory having the same address;  
11 an error checking and correction apparatus, the  
12 error apparatus generating a correction pattern identifying  
13 the location of an error in an addressed signal group and  
14 the associated error signals, the error apparatus  
15 generating a restore signal when the error is consistent  
16 with a failing bit location;  
17 a flag apparatus storing the associated  
18 correction pattern and the associated address in response  
19 to the restore signal, the flag apparatus generating an  
20 interrupt flag in response to the restore signal.

21  
22 **Please amend Claim 15 as follows.**

23  
24 15. **(Currently Amended)** The memory unit as recited  
25 in claim 14 wherein the stored correction pattern and the  
26 stored address are transferred to the central processor for  
27 restoration of the failing bit memory location when the  
28 central processing unit services the interrupt.

1           16.   **(Original)**       The memory unit as recited in  
2 claim 14 wherein the error checking and correction  
3 apparatus includes an all logic "1"s detection unit, the  
4 all logic "1"s detection unit determining when the signals  
5 stored in the main memory and in the error signal memory  
6 are all logic "1"s.

7  
8           17.   **(Original)**       The memory unit as recited in  
9 claim 14 wherein the main memory and the error checking and  
10 correction memory are implemented in a technology selected  
11 from the group consisting of flash technology and EEPROM  
12 technology.